

2MBI900VXA-120P-50

IGBT Modules

IGBT MODULE (V series) 1200V / 900A / 2 in one package

■ Features

- High speed switching
- Voltage drive
- Low Inductance module structure

■ Applications

- Inverter for Motor Drive
- AC and DC Servo Drive Amplifier
- Uninterruptible Power Supply
- Industrial machines, such as Welding machines



■ Maximum Ratings and Characteristics

● Absolute Maximum Ratings (at Tc=25°C unless otherwise specified)

Items	Symbols	Conditions	Maximum ratings	Units	
Inverter	Collector-Emitter voltage	V _{CEs}	1200	V	
	Gate-Emitter voltage	V _{GES}	±20	V	
	Collector current	I _c	Continuous	Tc=25°C 1200	A
				Tc=100°C 900	
		I _c pulse	1ms	1800	
		-I _c		900	
Collector power dissipation	P _c	-I _c pulse	1ms	1800	
		1 device		5100	W
Junction temperature	T _j		175	°C	
Operating junction temperature (under switching conditions)	T _{jop}		150		
Case temperature	T _c		150		
Storage temperature	T _{stg}		-40 ~ +150		
Isolation voltage	V _{iso}	between terminal and copper base (*1)	AC : 1min.	4000	VAC
		between thermistor and others (*2)			
Screw torque (*3)	Mounting	M5	6.0	N m	
	Main Terminals	M8	10.0		
	Sense Terminals	M4	2.1		

Note *1: All terminals should be connected together during the test.

Note *2: Two thermistor terminals should be connected together, other terminals should be connected together and shorted to base plate during the test.

Note *3: Recommendable Value : Mounting 3.0 ~ 6.0 Nm (M5) Recommendable Value : Main Terminals 8.0 ~ 10.0 Nm (M8)
Recommendable Value : Sense Terminals 1.8 ~ 2.1 Nm (M4)

● Electrical characteristics (at Tj= 25°C unless otherwise specified)

Items	Symbols	Conditions	Characteristics			Units	
			min.	typ.	max.		
Zero gate voltage collector current	I _{CEs}	V _{GE} = 0V, V _{CE} = 1200V	-	-	8.0	mA	
Gate-Emitter leakage current	I _{GES}	V _{CE} = 0V, V _{GE} = ±20V	-	-	1600	nA	
Gate-Emitter threshold voltage	V _{GE(th)}	V _{CE} = 20V, I _c = 900mA	6.0	6.5	7.0	V	
Collector-Emitter saturation voltage	V _{CE(sat)} (terminal) (*4)	V _{GE} = 15V I _c = 900A	Tj=25°C	-	1.75	2.20	V
			Tj=125°C	-	2.10	-	
			Tj=150°C	-	2.15	-	
	Tj=25°C		-	1.65	2.10		
	Tj=125°C		-	2.00	-		
	Tj=150°C		-	2.05	-		
Internal gate resistance	R _{g(int)}	-	-	1.19	-	Ω	
Input capacitance	C _{ies}	V _{CE} = 10V, V _{GE} = 0V, f = 1MHz	-	83	-	nF	
Turn-on time	ton	V _{CC} = 600V	-	1.00	-	μsec	
	tr	I _c = 900A	-	0.40	-		
	tr (i)	V _{GE} = ±15V	-	0.15	-		
Turn-off time	toff	R _G = 1.6Ω	-	1.20	-	μsec	
	tf	L _S = 70nH	-	0.15	-		
Forward on voltage	V _F (terminal) (*4)	V _{GE} = 0V I _F = 900A	Tj=25°C	-	1.90	2.35	V
			Tj=125°C	-	2.05	-	
			Tj=150°C	-	2.00	-	
	Tj=25°C		-	1.80	2.25		
	Tj=125°C		-	1.95	-		
	Tj=150°C		-	1.90	-		
Reverse recovery time	trr	I _F = 900A	-	0.20	-	μsec	
Thermistor	Resistance	R	T=25°C	-	5000	Ω	
			T=100°C	465	495		520
	B value	B	T=25/50°C	3305	3375	3450	K

Note *4: Please refer to page 6, there is definition of on-state voltage at terminal.

● Thermal resistance characteristics

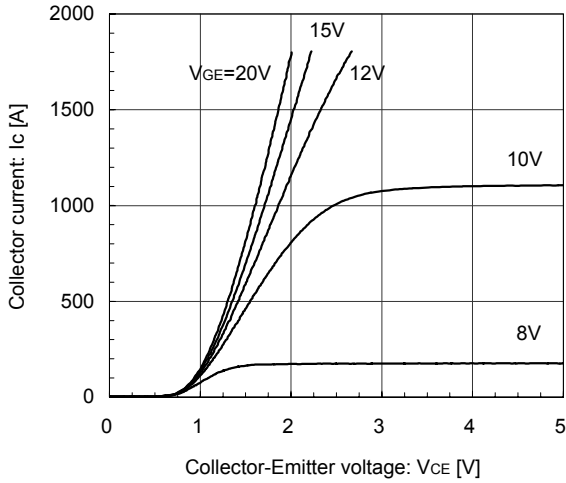
Items	Symbols	Conditions	Characteristics			Units
			min.	typ.	max.	
Thermal resistance (1device)	R _{th(j-c)}	Inverter IGBT	-	-	0.030	°C/W
		Inverter FWD	-	-	0.054	
Contact thermal resistance (1device) (*5)	R _{th(c-f)}	with Thermal Compound	-	0.00625	-	

Note *5: This is the value which is defined mounting on the additional cooling fin with thermal compound.

■ Characteristics (Representative)

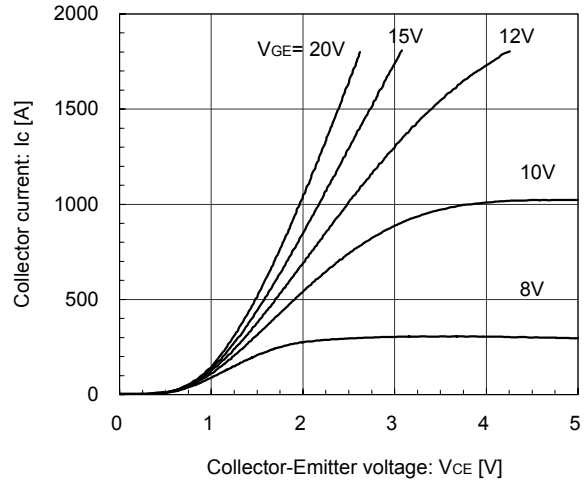
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
Tj= 25°C / chip



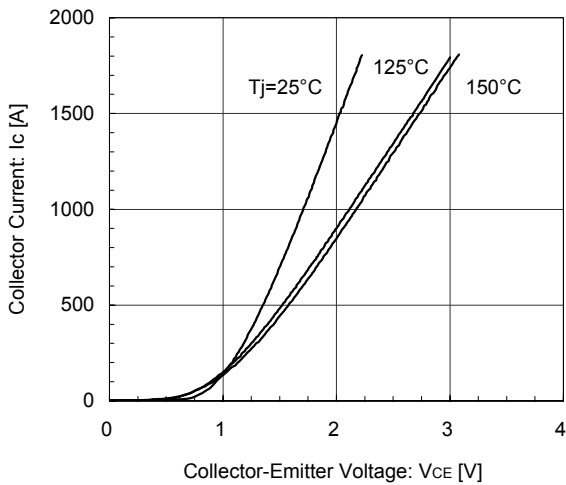
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
Tj= 150°C / chip



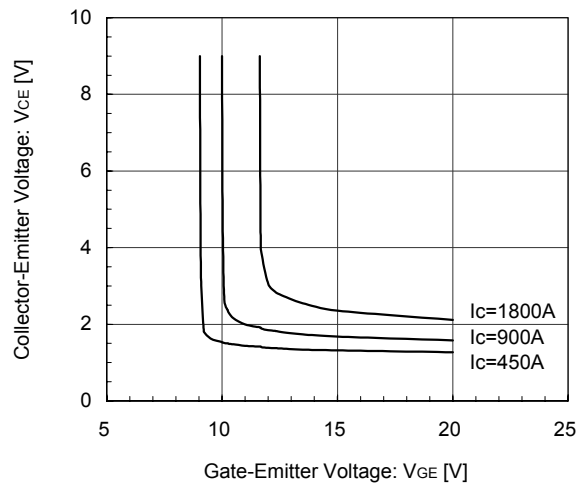
[INVERTER]

Collector current vs. Collector-Emittter voltage (typ.)
VGE= 15V / chip



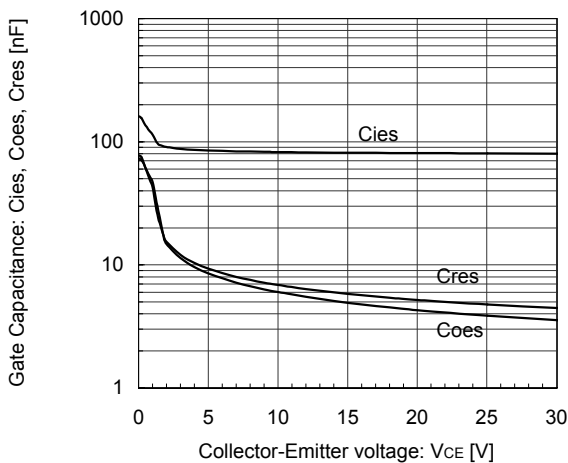
[INVERTER]

Collector-Emittter voltage vs. Gate-Emittter voltage (typ.)
Tj= 25°C / chip



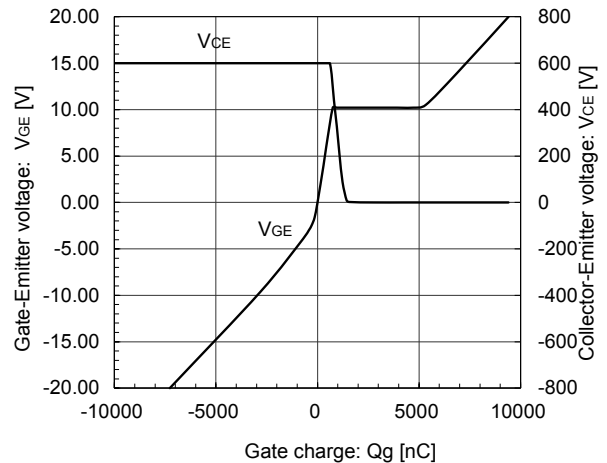
[INVERTER]

Gate Capacitance vs. Collector-Emittter Voltage (typ.)
VGE= 0V, f= 1MHz, Tj= 25°C



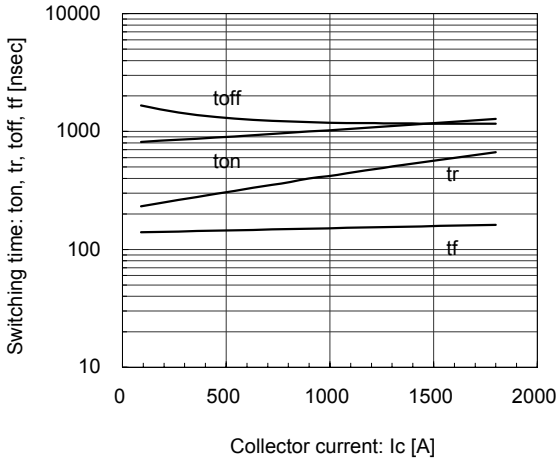
[INVERTER]

Dynamic Gate Charge (typ.)
Vcc=600V, Ic=900A, Tj= 25°C



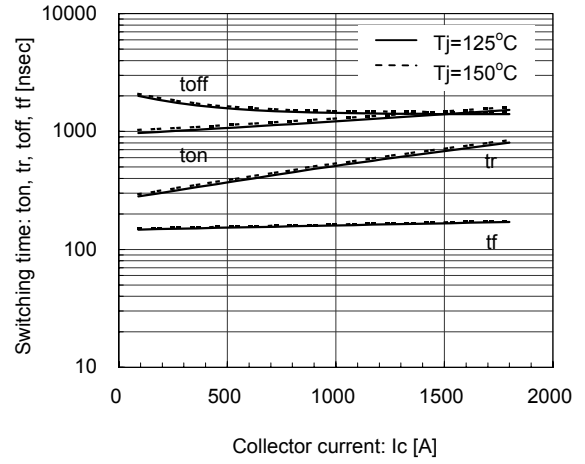
[INVERTER]

Switching time vs. Collector current (typ.)
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=1.6\Omega, T_J=25^\circ C$



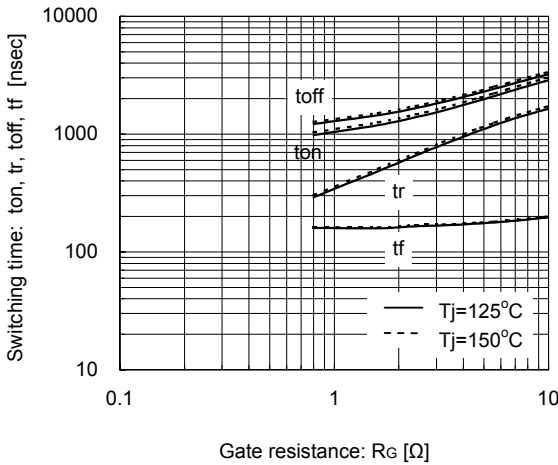
[INVERTER]

Switching time vs. Collector current (typ.)
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=1.6\Omega, T_J=125^\circ C, 150^\circ C$



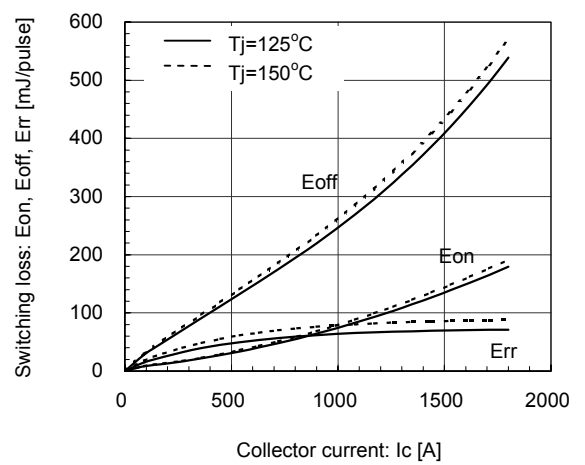
[INVERTER]

Switching time vs. Gate resistance (typ.)
 $V_{CC}=600V, I_c=900A, V_{GE}=\pm 15V, T_J=125^\circ C, 150^\circ C$



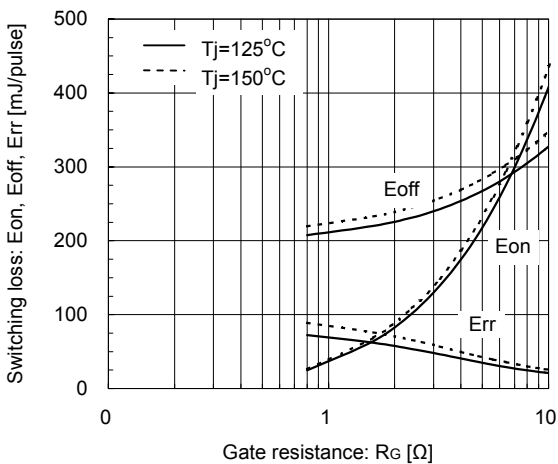
[INVERTER]

Switching loss vs. Collector current (typ.)
 $V_{CC}=600V, V_{GE}=\pm 15V, R_G=1.6\Omega, T_J=125^\circ C, 150^\circ C$



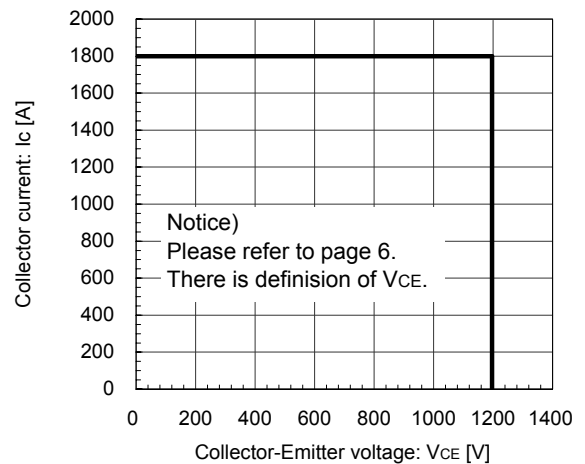
[INVERTER]

Switching loss vs. Gate resistance (typ.)
 $V_{CC}=600V, I_c=900A, V_{GE}=\pm 15V, T_J=125^\circ C, 150^\circ C$



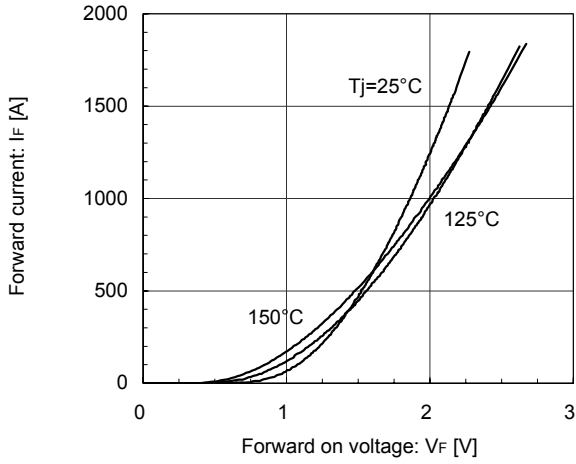
[INVERTER]

Reverse bias safe operating area (max.)
 $+V_{GE}=15V, -V_{GE}=15V, R_G=1.6\Omega, T_J=150^\circ C$



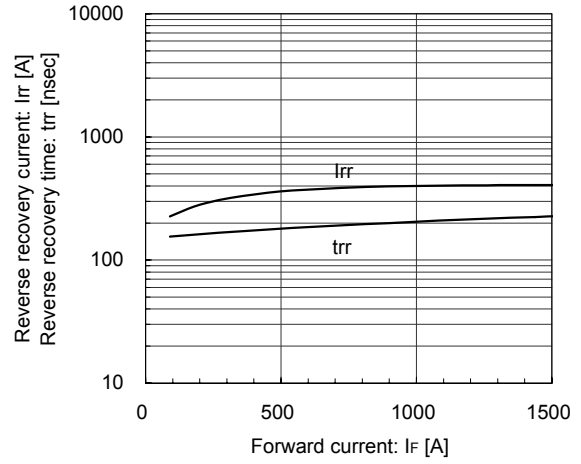
[INVERTER]

Forward Current vs. Forward Voltage (typ.)
chip



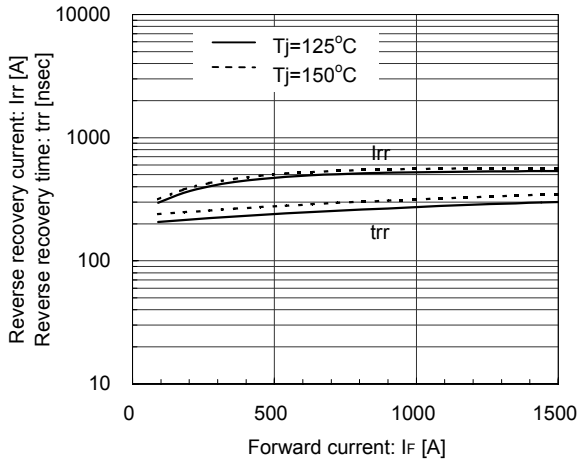
[INVERTER]

Reverse Recovery Characteristics (typ.)
 $V_{CC}=600\text{V}$, $V_{GE}=\pm 15\text{V}$, $R_G=1.6\Omega$, $T_j=25^\circ\text{C}$

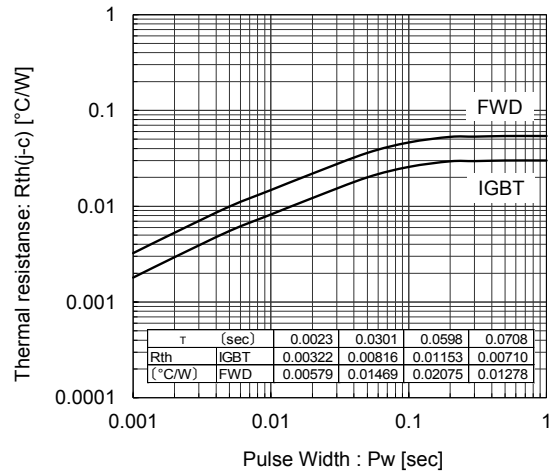


[INVERTER]

Reverse Recovery Characteristics (typ.)
 $V_{CC}=600\text{V}$, $V_{GE}=\pm 15\text{V}$, $R_G=1.6\Omega$, $T_j=125^\circ\text{C}$, 150°C

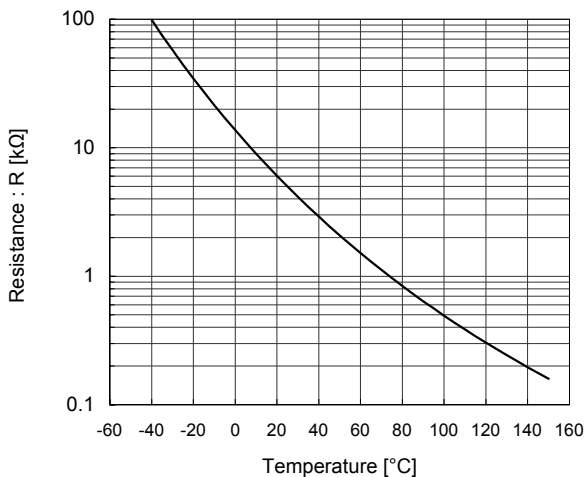


Transient Thermal Resistance (max.)



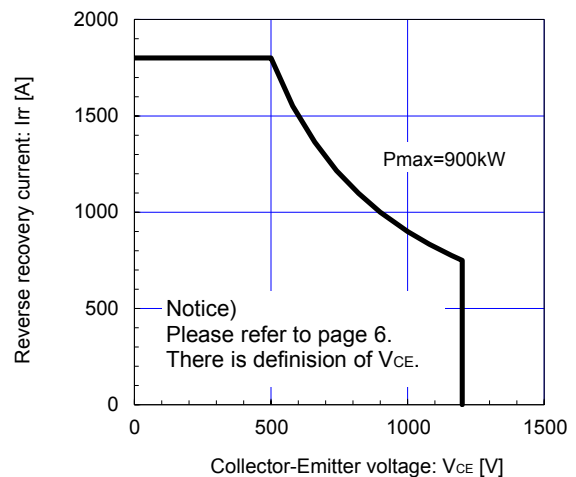
[THERMISTOR]

Temperature characteristic (typ.)

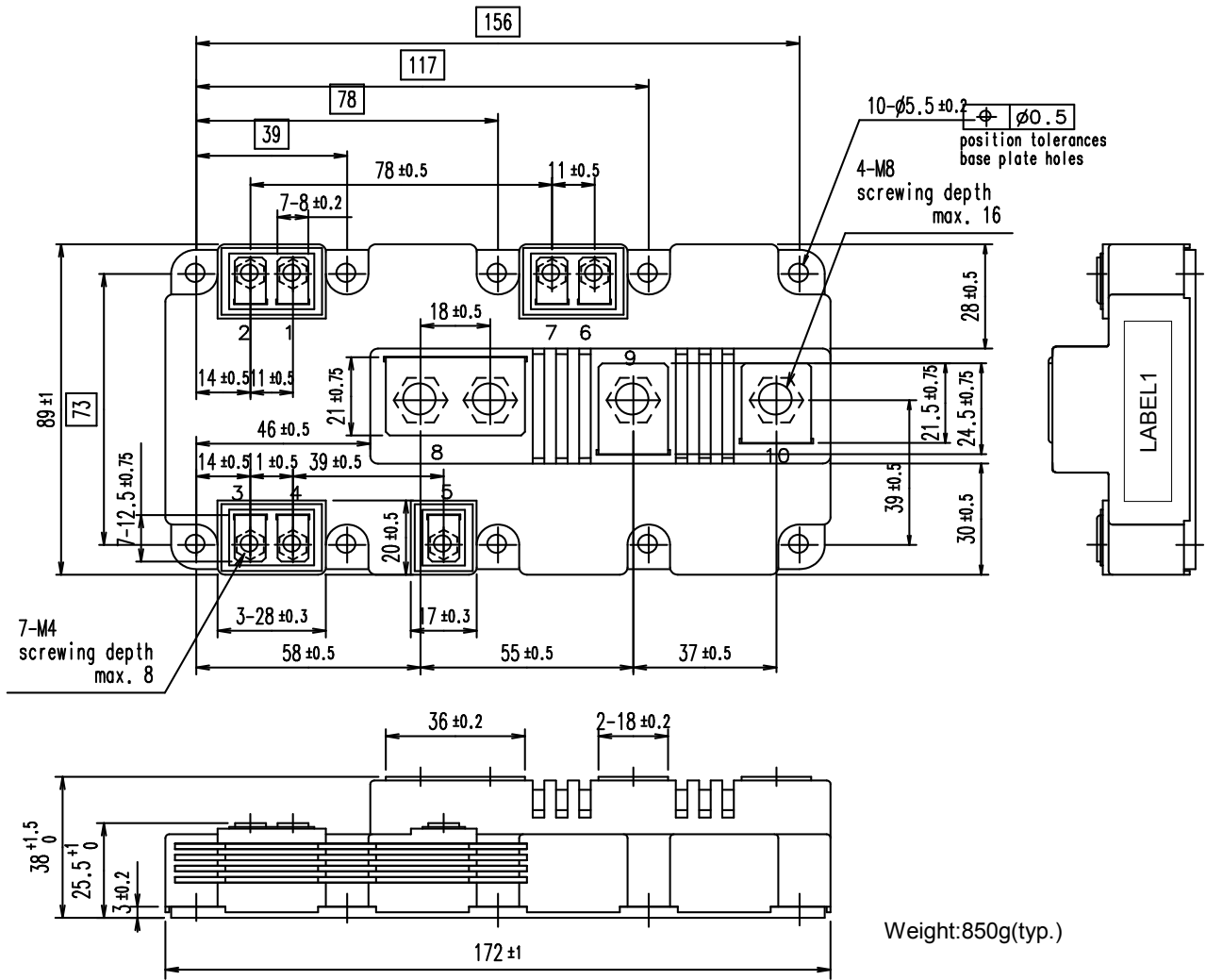


FWD safe operating area (max.)

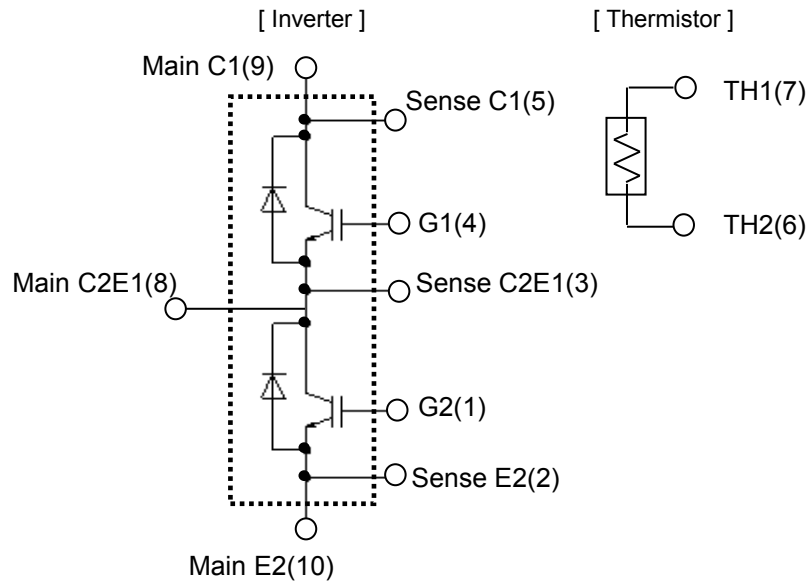
$T_j=150^\circ\text{C}$



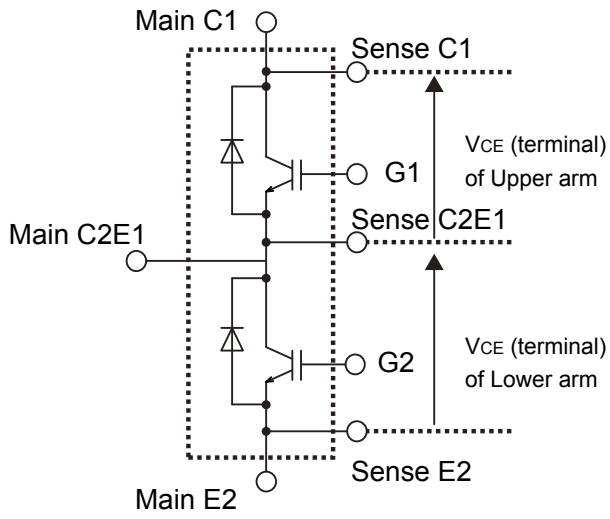
■ Outline Drawings (Unit: mm)



■ Equivalent Circuit



■ Definition of on-state voltage at terminal and switching characteristics



Fuji defined V_{CE} value of terminal by using Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Switching characteristics of V_{CE} also is defined between Sense C1 and Sense C2E1 for Upper arm and Sense C2E1 and Sense E2 for Lower arm .

Please use these terminals whenever measure spike voltage and on-state voltage .

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IGBT Modules

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